





Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C, SOT23
60V	$1.8\Omega @ V_{GS} = 5V$	470mA
60 V	$2.4\Omega @ V_{GS} = 3V$	470IIIA

Description and Applications

DMN61D8L/LVT provides a single component solution for switching inductive loads such as relays, solenoids, and small DC motors in automotive applications, without the need of a freewheeling diode. DMN61D8L/LVT accepts logic level inputs, thus allowing it to be driven by logic gates, inverters, and microcontrollers. It is ideally suited for doors, windows, and antenna relay coils.



Features and Benefits

 Provides a more reliable and robust interface between sensitive logic and DC relay coils

60V N-CHANNEL ENHANCEMENT MODE MOSFET

- Replaces 3 to 4 discrete components enabling PCB footprint to be reduced
- Internal active clamp removes the need for external zener diode
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- The Automotive-Compliant Parts are Available Under Separate Datasheets (<u>DMN61D8LQ</u> and <u>DMN61D8LVTQ</u>)

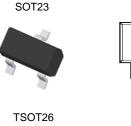
Mechanical Data

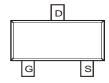
Case: SOT23

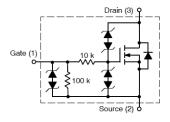
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe.
 (Lead-Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram
- Weight: 0.008 grams (Approximate)

Case: TSOT26

- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.013 grams (Approximate)











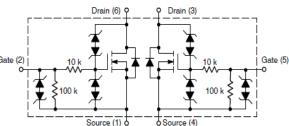
Top View





6 D1 5 G2

4 S2



Ordering Information (Note 4)

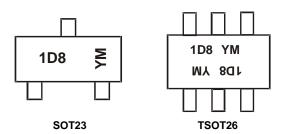
Part Number	Case	Packaging
DMN61D8L-7	SOT23	3,000/Tape & Reel
DMN61D8L-13	SOT23	10,000/Tape & Reel
DMN61D8LVT-7	TSOT26	3,000/Tape & Reel
DMN61D8LVT-13	TSOT26	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



1D8 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: F= 2018) M = Month (ex: 9 = September)

Date Code Key

	,												
Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	В	С	D	Е	F	G	Н		J	K	L	М	N
Mon	th	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Cod	le	1	2	3	4	5	6	7	8	9	0	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) SOT23	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	470 370	mA
Continuous Drain Current (Note 6) TSOT26	Steady State	T _A = +25°C T _A = +70°C	I _D	630 500	mA
Maximum Continuous Body Diode Forward Current	(Note 6)		I _S	0.5	А
Single Pulse Drain-to-Source Avalanche Energy (for relay coils/inductive loads of 80Ω or higher) (T _J initial = +85°C)			Ez	200	mJ
Peak Power Dissipation, Drain-to-Source (non-repetitive current square pulse 1.0ms duration) (T _J initial = +85°C)			Ррк	20	W
Load Dump Pulse, Drain-to-Source, R_{SOURCE} = 0.5 (for relay coils/inductive loads of 80Ω or higher) (T _J	-	,	E _{LD1}	60	V
Inductive Switching Transient 1, Drain-to-Source (Waveform: $R_{SOURCE} = 10\Omega$, $t = 2.0ms$) (for relay coils/inductive loads of 80Ω or higher) (T _J Initial = +85°C)			E _{LD2}	100	V
Inductive Switching Transient 2, Drain-to-Source (Waveform: $R_{SOURCE} = 4.0\Omega$, $t = 50\mu s$) (for relay coils/inductive loads of 80Ω or higher) (T _J Initial = +85°C)			E _{LD3}	300	V
Reverse Battery, 10 Minutes (Drain-to-Source) (for relay coils/inductive loads of 80Ω or higher)			Rev-Bat	-14	V
Dual Voltage Jump Start, 10 Minutes (Drain-to-Source)			Dual-Volt	28	V
ESD Human Body Model (HBM)			ESD	4,000	V



Thermal Characteristics (SOT23) ($@T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	390	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	321	°C/W
Total Power Dissipation (Note 6)		P _D	610	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	208	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Thermal Characteristics (TSOT26) ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P _D	820	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	154	°C/W
Total Power Dissipation (Note 6)		P _D	1090	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	116	°C/W
Operating and Storage Temperature Range	•	T _J , T _{STG}	-55 to +150	°C

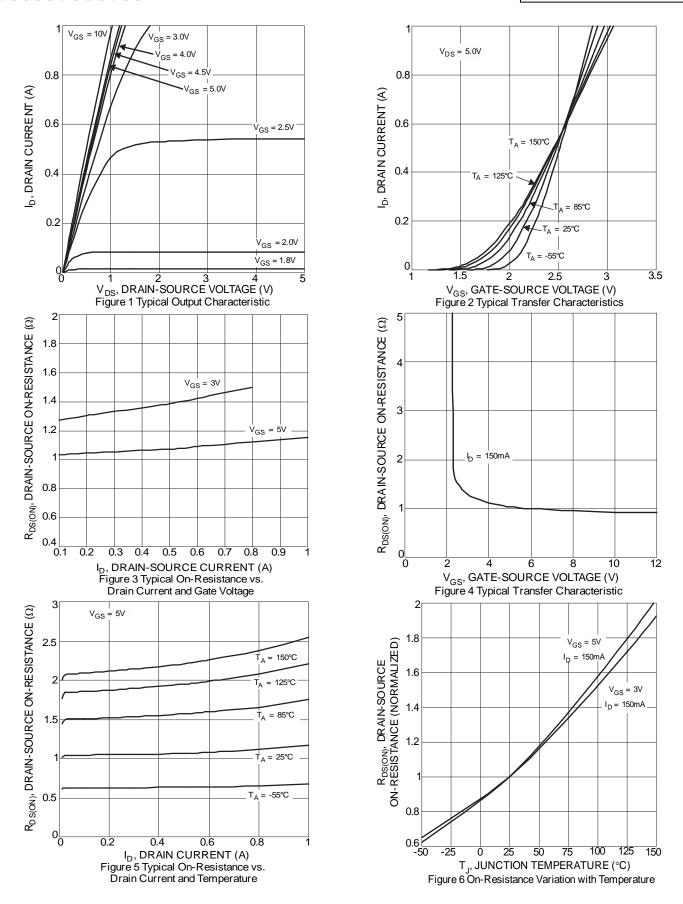
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	•					
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_D = 10mA$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	50 0.5	μΑ	$V_{DS} = 60V, V_{GS} = 0V$ $V_{DS} = 12V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±90 ±60	μA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$ $V_{GS} = \pm 3V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.3	_	2.0	V	$V_{DS} = V_{GS}$, $I_D = 1mA$
Static Drain-Source On-Resistance	5		1.1	1.8	Ω	$V_{GS} = 5V, I_D = 0.15A$
Static Dialif-Source Off-Resistance	R _{DS(ON)}	_	1.4	2.4	12	$V_{GS} = 3V, I_D = 0.15A$
Forward Transfer Admittance	Y _{fs}	80	_	_	ms	$V_{DS} = 12V, I_D = 0.15A$
Diode Forward Voltage	V_{SD}	_	_	1.2	V	$V_{GS} = 0V, I_S = 0.15A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	12.9	_	pF	
Output Capacitance	Coss	_	17		pF	$V_{DS} = 12V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C_{rss}	_	0.84	_	pF	1 - 1.51/11/2
Total Gate Charge	Qg	_	0.74	_	nC	57.77
Gate-Source Charge	Q _{gs}	_	0.19	_	nC	$V_{GS} = 5V, V_{DS} = 12V,$ $I_{D} = 150 \text{mA}$
Gate-Drain Charge	Q_{gd}	_	0.16	_	nC	1D = 130111A
Turn-On Delay Time	t _{D(ON)}	_	131	_	ns	
Turn-On Rise Time	t _R	_	301	_	ns	\\ 12\\ \\alpha = 5\\
Turn-Off Delay Time	t _{D(OFF)}	_	582	_	ns	$V_{DD} = 12V, V_{GS} = 5V$
Turn-Off Fall Time	t _F	_	440	_	ns	

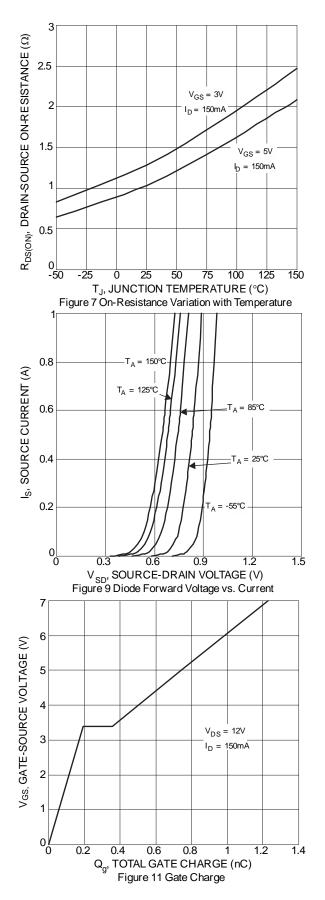
Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

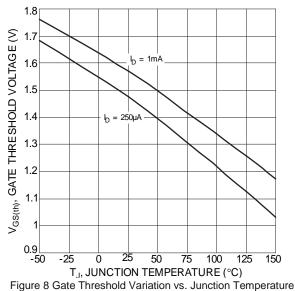
Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





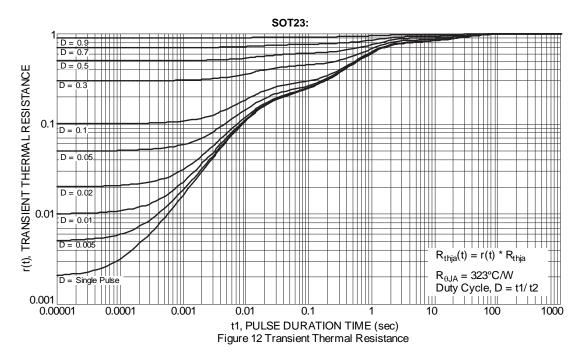


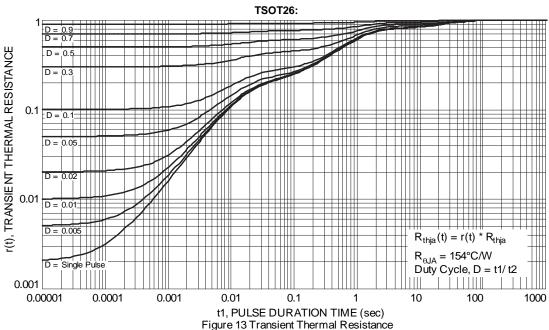




100 | f = 1MHz | f = 1MHz | C_{iss} | C_{iss} | C_{rss} | C_{rs} | C_{rs} | C_{rs} | C_{rs} | C_{rs} | C_{rss} | C_{rs} | C_r





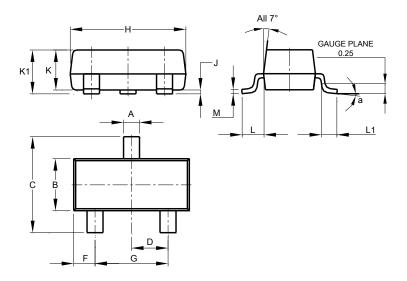




Package Outline Dimensions

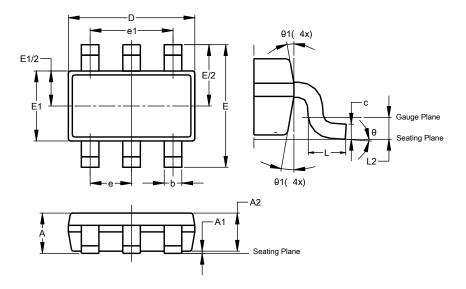
Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	0°	8°			
All	Dimens	ions in	mm		

TSOT26



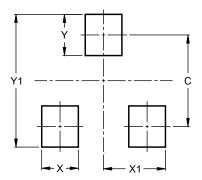
TSOT26						
Dim	Min	Max	Тур			
Α	-	1.00	_			
A1	0.010	0.100	_			
A2	0.840	0.900	_			
D	2.800	3.000	2.900			
E	2	2.800 BSC				
E1	1.500	1.700	1.600			
b	0.300	0.450	_			
С	0.120	0.200	_			
е	0	0.950 BSC				
e1	1	.900 BS	C			
L	0.30	0.50	-			
L2	0	.250 BS	C			
θ	0°	8°	4°			
θ1	4°	12°	-			
Α	II Dimen	sions in	mm			



Suggested Pad Layout

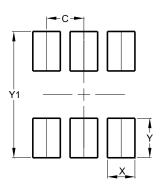
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SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9

TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199



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